

R-C Thermal Model Parameters

DESCRIPTION

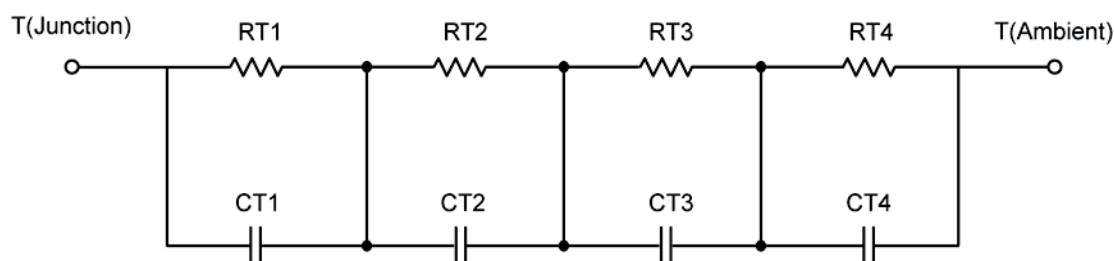
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

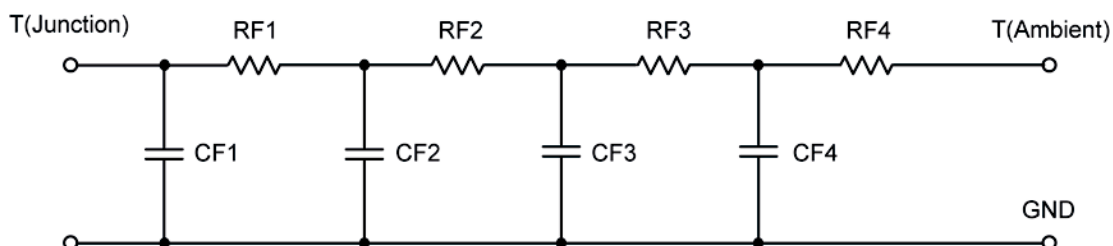
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	970.7997 m	1.3946 m	N/A
RT2	12.3687	1.1273	N/A
RT3	8.0678	328.6545 m	N/A
RT4	43.1324	342.3480 m	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	2.8671 m	61.0179 u	N/A
CT2	473.2983 m	35.9873 m	N/A
CT3	41.1219 m	105.5840 m	N/A
CT4	1.8042	3.8344 m	N/A

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION

R-C VALUES FOR FILTER CONFIGURATION

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	4.3418	20.3860 m	N/A
RF2	8.9030	454.8081 m	N/A
RF3	18.6817	511.8163 m	N/A
RF4	32.8015	814.7368 m	N/A
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	12.3440 m	3.2870 m	N/A
CF2	69.0457 m	241.6543 u	N/A
CF3	439.0398 m	25.2168 m	N/A
CF4	1.9299	2.6853 m	N/A

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

